

Din-Tek

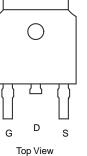
RoHS

COMPLIANT

N-Channel 200 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω) Max.	(Ω) Max. I _D (A)		
200	0.45 at V _{GS} = 10 V	10	15	
	0.47 at V _{GS} = 4.5 V	6.2	15	

TO-252

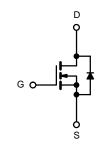


FEATURES

- DT-Trench Power MOSFET
- 100 % $\rm R_g$ and UIS Tested
- Material categorization:

APPLICATIONS

- DC/DC Converters
- DC/AC Inverters
- Motor Drives



N-Channel MOSFET

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	200	v		
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current	T _C = 25 °C		10		
Continuous Drain Current	T _C = 70 °C	I _D	7.2	_	
Pulsed Drain Current (t = 300 µs)		I _{DM}	25	- A	
Avalanche Current	I _{AS}	3.5			
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	51.25	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	Р	91.7 ^b	W	
	T _A = 25 °C ^c	P _D	2.1	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	60	°C/W	
Junction-to-Case (Drain)	R _{thJC}	3	0/10	

Notes:

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.c. When mounted on 1" square PCB (FR-4 material).

d. Base on T_C = 25 °C.





Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	200			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	1.2		3	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 250	nA
Zero Gate Voltage Drain Current		V _{DS} = 200 V, V _{GS} = 0 V			1	μA
	I _{DSS}	$V_{DS} = 200 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 \text{ °C}$			50	
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 150 °C			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	10			А
Drain-Source On-State Resistance ^a	D	V _{GS} = 10 V, I _D = 6.6 A		0.45	0.510	Ω
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 6 \text{ A}$		0.47	0.530	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 6.6 A		25		S
Dynamic ^b	•	·		•		
Input Capacitance	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		760		pF
Output Capacitance	C _{oss}			85		
Reverse Transfer Capacitance	C _{rss}			40		
Total Gate Charge ^c	Qg			19.8	30	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 6.6 \text{ A}$		3.6		
Gate-Drain Charge ^c	Q _{gd}			4.1		
Gate Resistance	Rg	f = 1 MHz	0.4	2	4	Ω
Turn-On Delay Time ^c	t _{d(on)}			8	16	
Rise Time ^c	t _r	V_{DD} = 50 V, R_{L} = 9.6 Ω		11	20	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 5.2$ Å, $V_{GEN} = 10$ V, $R_g = 1 \Omega$		18	27	
Fall Time ^c	t _f			5	10	
Turn-On Delay Time ^c	t _{d(on)}			38	57	ns
Rise Time ^c	t _r	V_{DD} = 50 V, R_{L} = 9.6 Ω		58	87	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 5.2$ Å, $V_{GEN} = 4.5$ V, $R_g = 1 \Omega$		18	27	
Fall Time ^c	t _f			8	16	
Drain-Source Body Diode Ratings a	nd Characteri	stics ^b T _C = 25 °C				
Continuous Current	۱ _S				10	^
Pulsed Current	I _{SM}				15	A
Forward Voltage ^a	V _{SD}	$I_F = 5.2 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.5	V
Reverse Recovery Time	t _{rr}			34	51	ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 5.2 A, dl/dt = 100 A/µs		3	5	Α
Reverse Recovery Charge	Q _{rr}	<u> </u>		50	75	nC

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

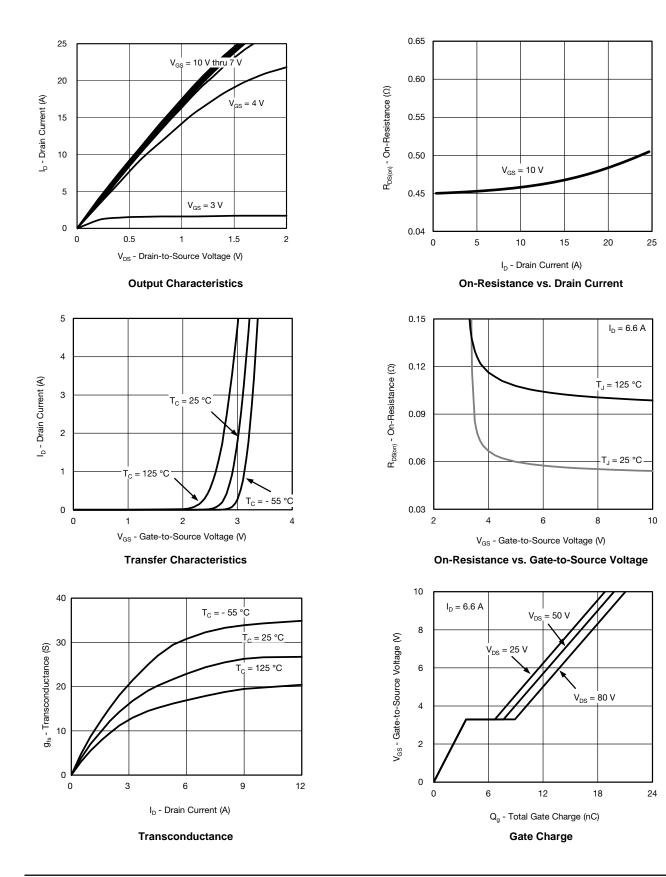
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

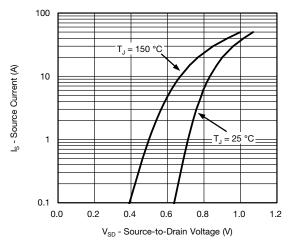


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

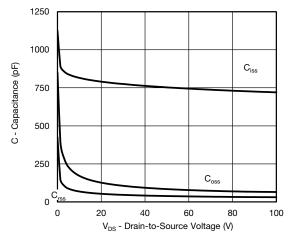




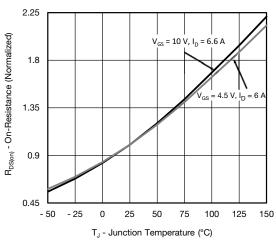
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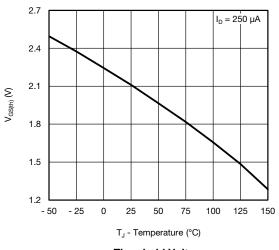
Source-Drain Diode Forward Voltage



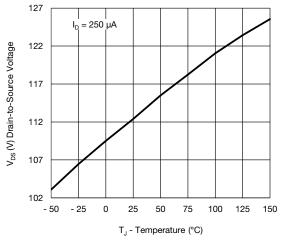




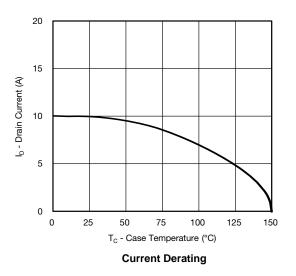
On-Resistance vs. Junction Temperature



Threshold Voltage

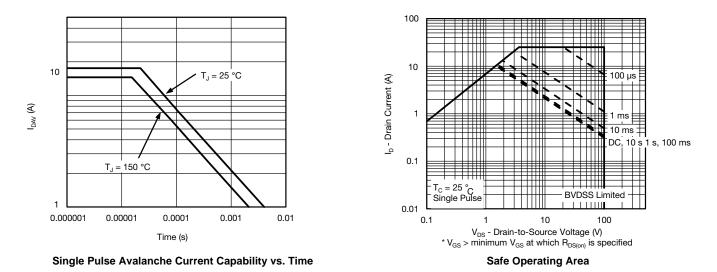


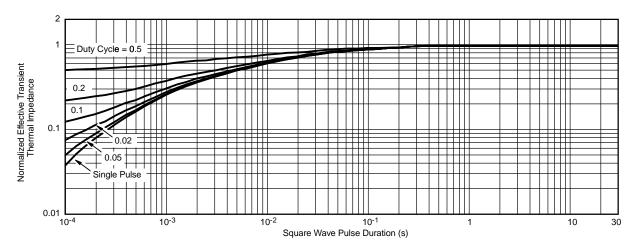
Drain Source Breakdown vs. Junction Temperature





TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Normalized Thermal Transient Impedance, Junction-to-Case



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